





#### 25V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C	
25V	4Ω @ V <sub>GS</sub> = 4.5V	0.32A	
250	5Ω @ V <sub>GS</sub> = 2.7V	0.28A	

## **Description**

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Load switch
- Portable applications
- Power Management Functions

#### **Features**

- 0.4mm ultra low profile package for thin application
- 0.48mm<sup>2</sup> package footprint, 16 times smaller than SOT23
- Low V<sub>GS(th)</sub>, can be driven directly from a battery
- Low R<sub>DS(on)</sub>
- ESD Protected Gate (>6kV Human Body Mode)
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

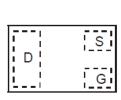
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.00043 grams (approximate)



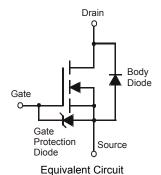
X2-DFN0806-3



**Bottom View** 



Top View Package Pin Configuration



# Ordering Information (Note 4)

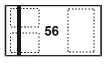
Ī	Part Number	Compliance	Case	Packaging
	DMN25D0UFA-7B	Standard	X2-DFN0806-3	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and 4.1000ppm antimony compounds.
   4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

DMN25D0UFA-7B



Top View Bar Denotes Gate and Source Side

56 = Product Type Marking Code



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		$V_{DSS}$	25	V
Gate-Source Voltage		$V_{GSS}$	V <sub>GSS</sub> 8	
	(Note 6)	,	0.32	А
Continuous Drain Current, V <sub>GS</sub> = 4.5V	$T_A = +70^{\circ}C \text{ (Note 6)}$	ID	0.25	
	(Note 5)	ID	0.24	Α
Pulsed Drain Current	(Note 7)	I <sub>DM</sub>	1.2	Α

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	Б	0.63	- W	
Power Dissipation	(Note 5)	P <sub>D</sub>	0.28		
Thermal Resistance, Junction to Ambient	(Note 6)	Б	201	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	338		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

# Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

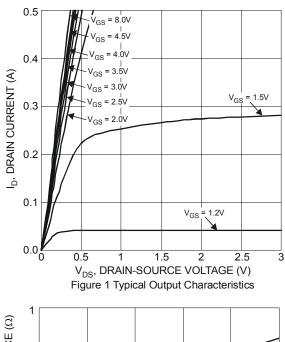
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	25	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	100	nA	V <sub>GS</sub> = 8V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.6	_	1.2	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	Б	_	_	4	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.4A	
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	_	_	5	12	V <sub>GS</sub> = 2.7V, I <sub>D</sub> = 0.2A	
Forward Transfer Admittance	Y <sub>fs</sub>	_	1	-	S	$V_{DS} = 5V, I_D = 0.4A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.76	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.29A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	27.9	_	pF		
Output Capacitance	Coss	_	6.1	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2	_	pF		
Gate Resistance	Rg	_	26.4	_	Ω	$V_{DS}$ = 0V, $V_{GS}$ = 0V, f = 1MHz	
Total Gate Charge	Qg	_	0.36	_	nC		
Gate-Source Charge	Qgs	_	0.06	_	nC	$V_{DS} = 5V, V_{GS} = 4.5V,$	
Gate-Drain Charge	Q <sub>gd</sub>	_	0.04	_	nC	$I_D = 0.2A$	
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.9	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	1.8	_	ns	$V_{DS} = 6V$ , $V_{GS} = 4.5V$ , $I_{D} = 0.5A$ , $R_{G} = 50\Omega$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	6.6	_	ns		
Turn-Off Fall Time	t <sub>f</sub>	_	2.3	_	ns		

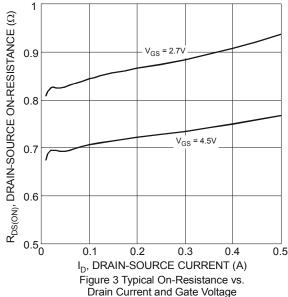
Notes:

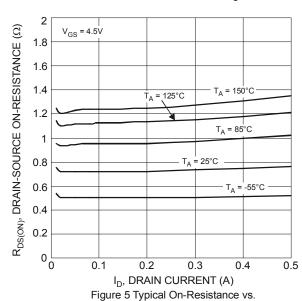
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  Short duration pulse test used to minimize self-heating effect.

- 8. Guaranteed by design. Not subject to production testing.

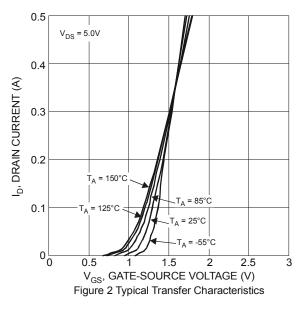


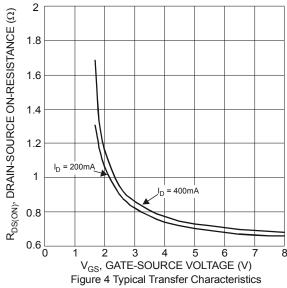


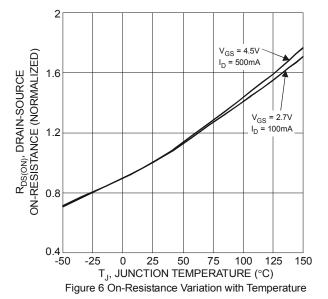




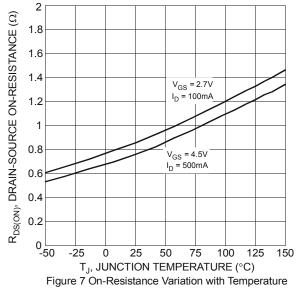
Drain Current and Temperature

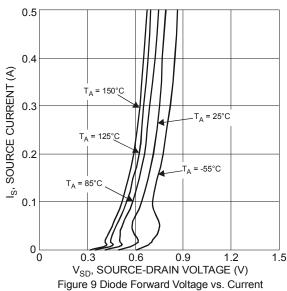


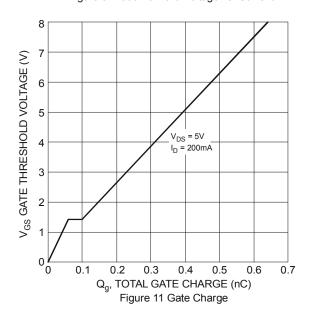












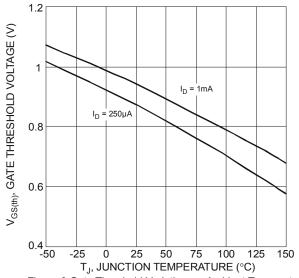
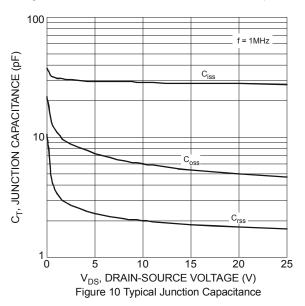
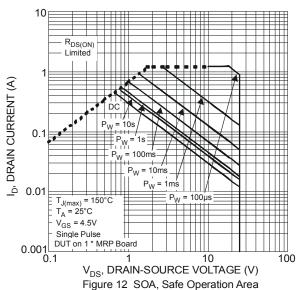
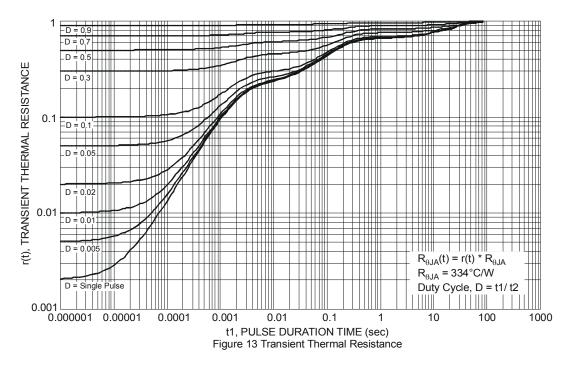


Figure 8 Gate Threshold Variation vs. Ambient Temperature



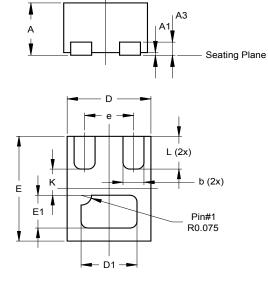






# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

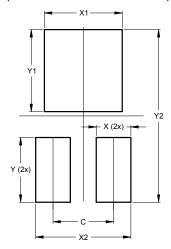


X2-DFN0806-3					
Dim	Min	Max	Тур		
Α	0.375	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.10		
b	0.10	0.20	0.15		
D	0.55	0.65	0.60		
D1	0.35	0.45	0.40		
E	0.75	0.85	0.80		
E1	0.20	0.30	0.25		
е	-	-	0.35		
K	-	-	0.20		
L	0.20	0.30	0.25		
All Dimensions in mm					



#### Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.350			
Х	0.200			
X1	0.450			
X2	0.550			
Y	0.375			
Y1	0.475			
Y2	1.000			

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